



FM24C1024A

2-Wire Serial EEPROM

Data Sheet

Oct. 2024



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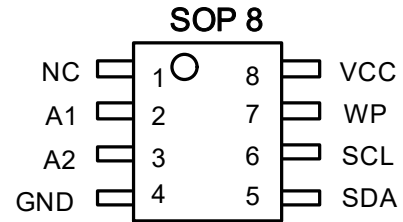
Description

FM24C1024A provides wide voltage of 1,048,576 bits of serial electrically erasable and programmable read-only memory (EEPROM) organized as 131,072 words of 8 bits each. the device can be connected in series to achieve the characteristics of the four devices to share a two-wire system addressable bus. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operations are essential.

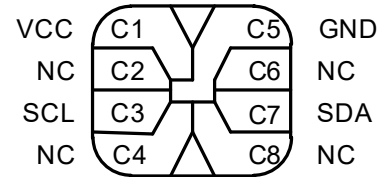
Features

- Low Operation Voltage: $V_{CC} = 1.7V$ to 5.5V
- Internally Organized: $131,072 \times 8$ (1024K)
- Two-wire Serial Interface
- Schmitt Trigger, Filtered Inputs for Noise Suppression
- Bi-directional Data Transfer Protocol
- 1MHz (2.5V, 5.5V) and 400 kHz (1.7V) Compatibility
- Write Protect Pin for Hardware Data Protection
- 256-byte Page Write Modes (Partial Page Writes are Allowed)
- Self-timed Write Cycle (5ms max)
- Operating Temperature range:
 - $-40^{\circ}C$ to $+85^{\circ}C$
- High-reliability
 - Endurance: 1,000,000 Write Cycles
 - Data Retention: 40 Years
- SOP8, TSSOP8 Packages (RoHS Compliant and Halogen-free)

Packaging Type



Module package (8 Pin)



Absolute Maximum Ratings

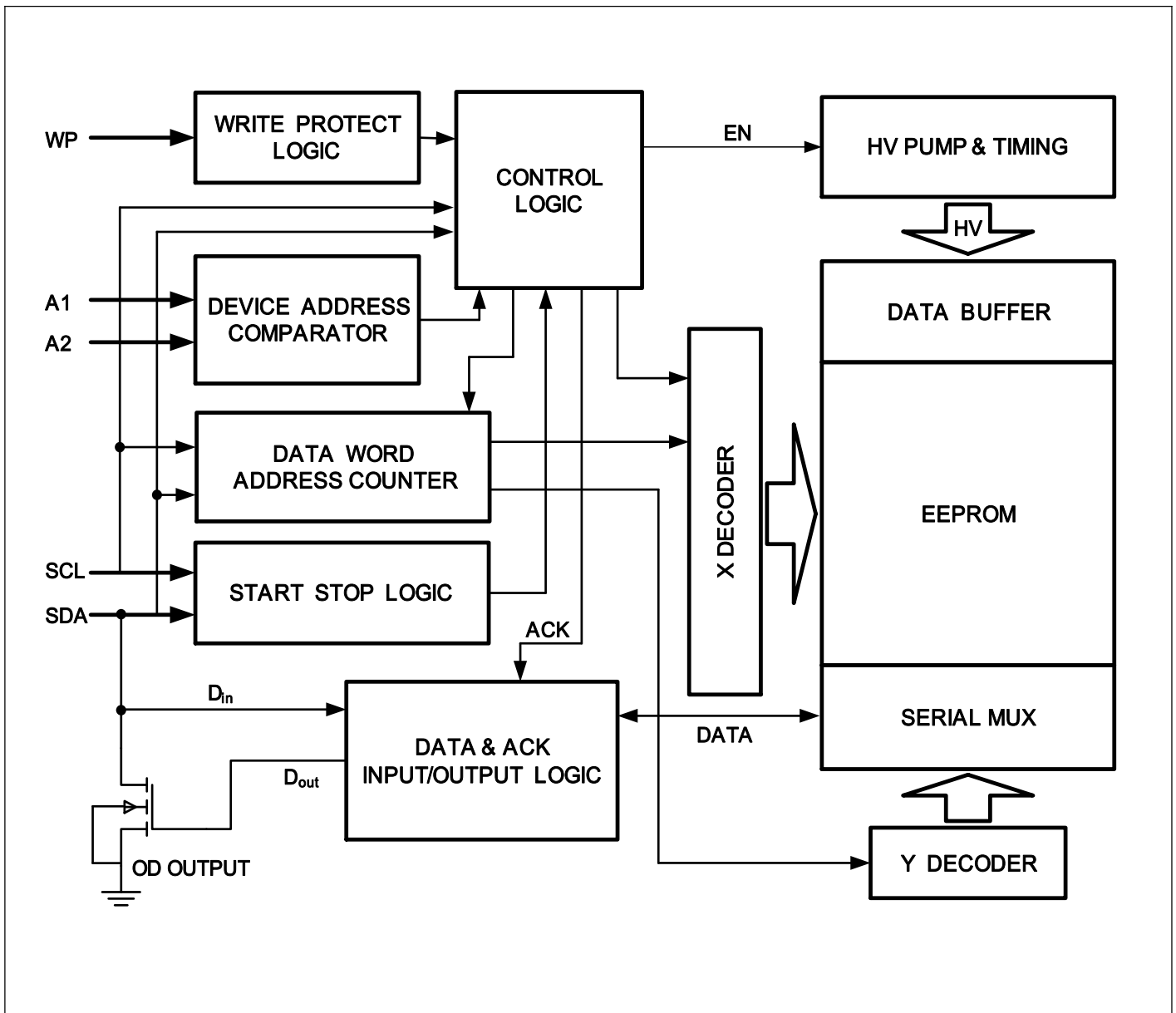
Operating Temperature (Plastic Package)	$-55^{\circ}C$ to $+125^{\circ}C$
Operating Temperature (Module Package)	$-20^{\circ}C$ to $+60^{\circ}C$
Storage Temperature (Plastic Package)	$-65^{\circ}C$ to $+150^{\circ}C$
Storage Temperature (Module Package)	$-25^{\circ}C$ to $+70^{\circ}C$
Voltage on Any Pin with Respect to Ground	$-0.5V$ to $+7.0V$
Maximum Operating Voltage	6.25V
DC Output Current	5.0 mA

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Pin Configurations

Pin Name	Function
A1~A2	Device Address Inputs
SDA	Serial Data Input/Output
SCL	Serial Clock Input
WP	Write Protect
VCC	Power Supply
GND	Ground
NC	Not Connect

Figure 1. Block Diagram



Pin Description

SERIAL CLOCK (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

SERIAL DATA (SDA): The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open-collector devices.

DEVICE ADDRESSES (A2, A1): The A2, and A1 pins are device address inputs that are hardwired or left not connected for hardware compatibility with other FM24CXX devices. When the pins are hardwired, as many as four 1024K devices may be addressed on a single bus system (device

addressing is discussed in detail under the Device Addressing section). If these pins are left floating, the A2, A1 pins will be internally pulled down to GND if the capacitive coupling to the circuit board V_{CC} plane is $<3\text{pF}$, if coupling is $>3\text{pF}$, FMSH recommends always connecting the address pins to GND.

WRITE PROTECT (WP): The FM24C1024A has a Write Protect pin that provides hardware data protection. The WP pin allows normal write operations when connected to ground (GND). When the Write Protect pin is connected to V_{CC} , all write operations to the memory are inhibited.

Write Protect Description

WP Pin Status	Part of the Memory Protected
WP = V_{CC}	Full Memory Protected
WP = GND	No Protected

Write-protect condition: The WP pin must be connected to V_{CC} from start condition in the write operation (byte write, page write) until stop condition (refer to Figure 11).

Non-write-protect condition: The WP pin must be connected to GND from start condition in the write operation (byte write, page write) until stop condition (refer to Figure 12).

In not using the write protect, connect the WP pin to GND or set it open. The write protect is valid in the range of operation power supply voltage. If the WP pin changes during this time, the address data being written at this time is not guaranteed. Regarding the timing of write protect, refer to Figure 3.

Memory Organization

FM24C1024A, 1024K SERIAL EEPROM: Internally organized with 512 pages of 256 bytes each, the 1024K requires a 17-bit data word address for random word addressing.

Pin Capacitance

SYMBOL	PARAMETER	CONDITIONS	Max	Units
$C_{IN}^{(1)}$	Input Capacitance	$V_{IN} = 0V, f = 1MHz$	6	pF
$C_{OUT}^{(1)}$	Output Capacitance	$V_{OUT} = 0V, f = 1MHz$	8	pF

Note: 1. This parameter is characterized and is not 100% tested.

DC Characteristics

Applicable over recommended operating range from: $T_A = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = +1.7V$ to $+5.5V$, (unless otherwise noted).

Symbol	Parameter	Test Condition	Min	Max	Units
V_{CC}	Supply Voltage		1.7	5.5	V
I_{CC1}	Supply Current	$V_{CC} = 5.0V$, Read at 400K		1.0	mA
I_{CC2}	Supply Current	$V_{CC} = 5.0V$, Write at 400K		3.0	mA
I_{SB}	Standby Current	$V_{IN} = V_{CC}/V_{SS}$		20.0	μA
I_{LI}	Input Leakage Current	$V_{IN} = V_{CC}/V_{SS}$		3.0	μA
I_{LO}	Output Leakage Current	$V_{OUT} = V_{CC}/V_{SS}$, SDA in Hi-Z		3.0	μA
V_{IL}^1	Input Low Level		-0.45	$V_{CC} \times 0.3$	V
V_{IH}^1	Input High Level		$V_{CC} \times 0.7$	$V_{CC} + 0.5$	V
V_{OL2}	Output Low Level	$V_{CC} = 1.7V, I_{OL} = 0.15 mA$		0.2	V
V_{OL1}	Output Low Level	$V_{CC} = 3.0V, I_{OL} = 2.1 mA$		0.4	V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

AC Characteristics

Applicable over recommended operating range from: $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{CC} = +1.7\text{V}$ to $+5.5\text{V}$, $C_L = 100\text{ pF}$ (unless otherwise noted). Test conditions are listed in Note 2.

Symbol	Parameter	1.7-volt		2.5-volt		5.5-volt		Units
		Min	Max	Min	Max	Min	Max	
f_{SCL}	Clock Frequency, SCL		400		1000		1000	kHz
t_{LOW}	Clock Pulse Width Low	1300		400		400		ns
t_{HIGH}	Clock Pulse Width High	600		400		400		ns
$t_I^{(1)}$	Noise Suppression Time		100		50		50	ns
t_{AA}	Clock Low to Data Out Valid	20	900	20	550	20	550	ns
$t_{BUF}^{(1)}$	Time the bus must be free before a new transmission can Start	1300		500		500		ns
$t_{HD,STA}$	Start Hold Time	600		250		250		ns
$t_{SU,STA}$	Start Setup Time	600		250		250		ns
$t_{HD,DAT}$	Data In Hold Time	0		0		0		ns
$t_{SU,DAT}$	Data In Setup Time	100		100		100		ns
t_R	Inputs Rise Time		300		300		300	ns
t_F	Inputs Fall Time		300		100		100	ns
$t_{SU,STO}$	Stop Setup Time	600		250		250		ns
t_{DH}	Data Out Hold Time	20		20		20		ns
t_{WS1}	WP setup time	1		1		1		us
t_{WH1}	WP hold time	1		1		1		us
t_{WS2}	WP release setup time	1		1		1		us
t_{WH2}	WP release hold time	1		1		1		us
t_{WR}	Write Cycle Time		5		5		5	ms
Endurance ⁽¹⁾	3.3V, 25°C, Page Mode	1,000,000						Write Cycles

Notes: 1. This parameter is characterized and is not 100% tested.

2. AC measurement conditions:

RL (connects to V_{CC}): 1.3 k Ω

Input pulse voltages: 0.3 V_{CC} to 0.7 V_{CC}

Input rise and fall times: $\leq 50\text{ ns}$

Input and output timing reference voltages: 0.5 V_{CC}

Device Operation

CLOCK and DATA TRANSITIONS: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (refer to Figure 4). Data changes during SCL high periods will indicate a start or stop condition as defined below.

START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (refer to Figure 5).

STOP CONDITION: A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (refer to Figure 5).

ACKNOWLEDGE: All address and data words are serially transmitted to and from the EEPROM in 8-bit

words. The EEPROM sends a zero during the ninth clock cycle to acknowledge that it has received each word.

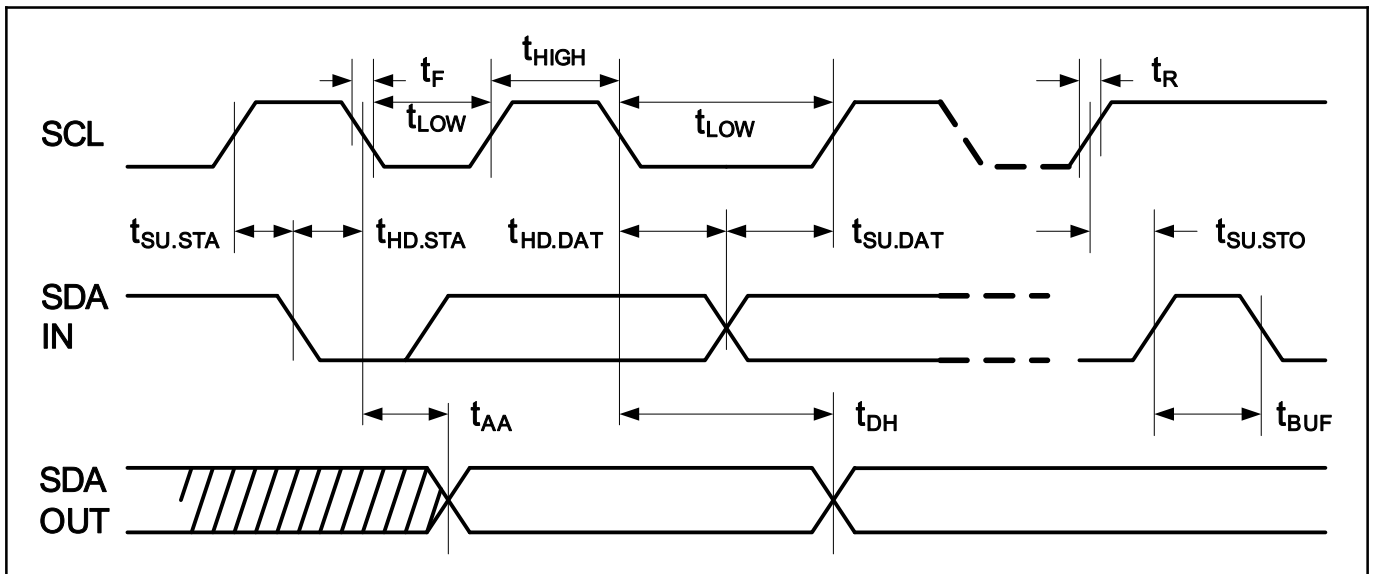
STANDBY MODE: The FM24C1024A features a low-power standby mode which is enabled: (a) upon power-up and (b) after the receipt of the stop bit and the completion of any internal operations.

Memory RESET: After an interruption in protocol, power loss or system reset, any two-wire part can be reset in following these steps:

1. Clock up to 9 Cycles,
2. Look for SDA high in each cycle while SCL is high and then,
3. Create a start condition as SDA is high.

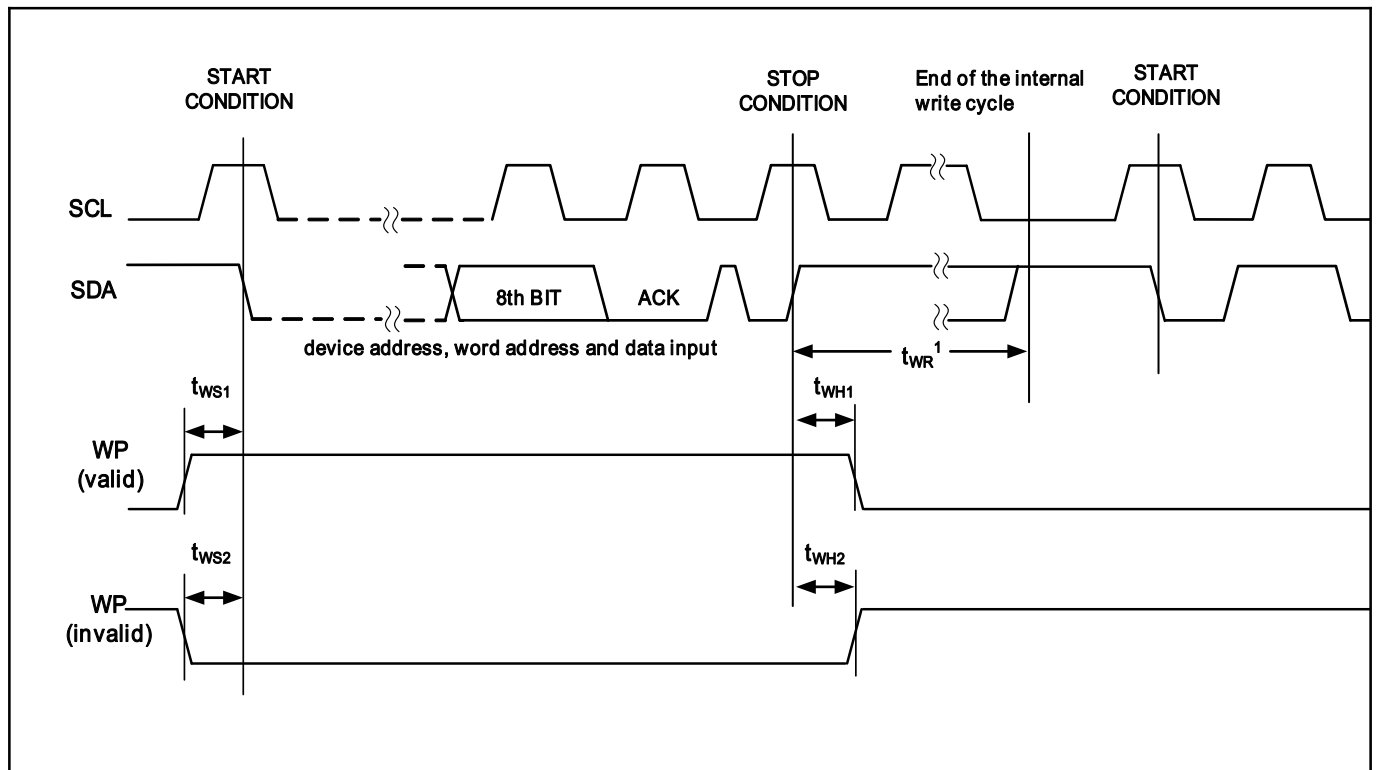
Bus Timing

Figure 2. SCL: Serial Clock, SDA: Serial Data I/O



Write Cycle Timing

Figure 3. SCL: Serial Clock, SDA: Serial Data I/O



Note: 1. The write cycle time t_{WR} is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

Figure 4. Data Validity

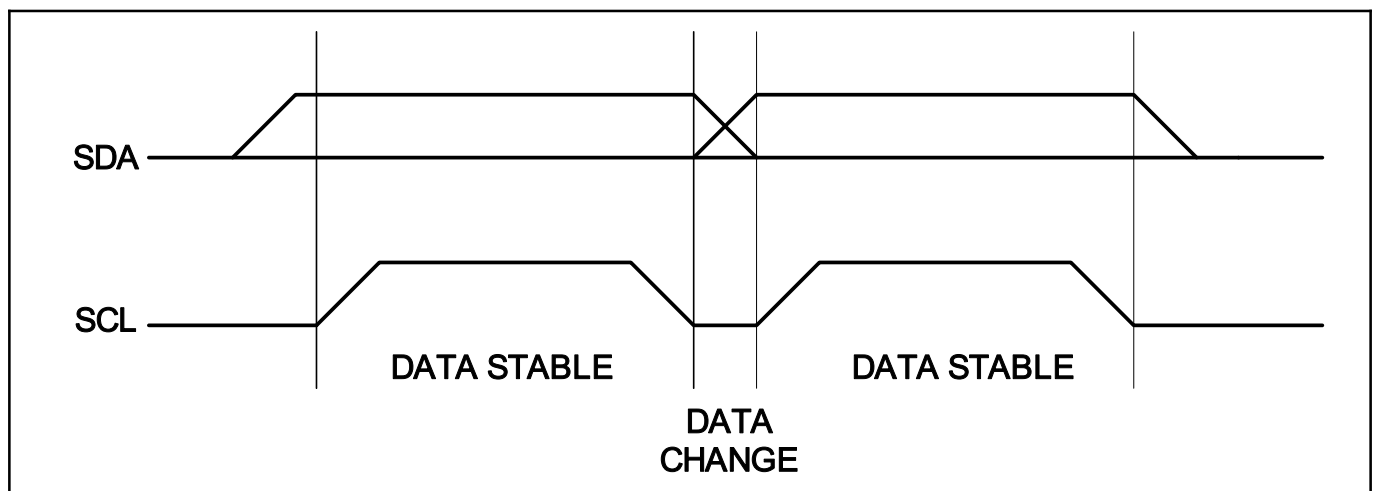


Figure 5. Start and Stop Definition

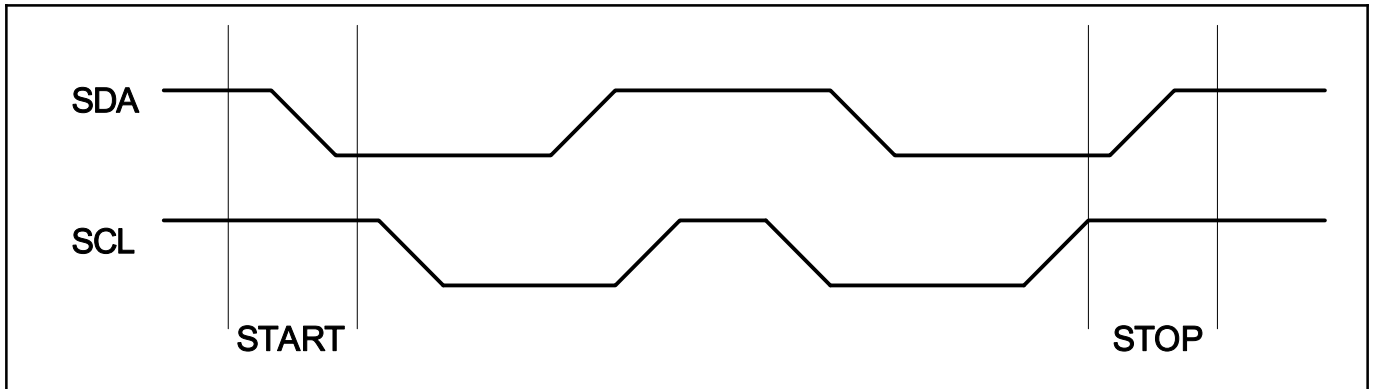


Figure 6. Output Acknowledge

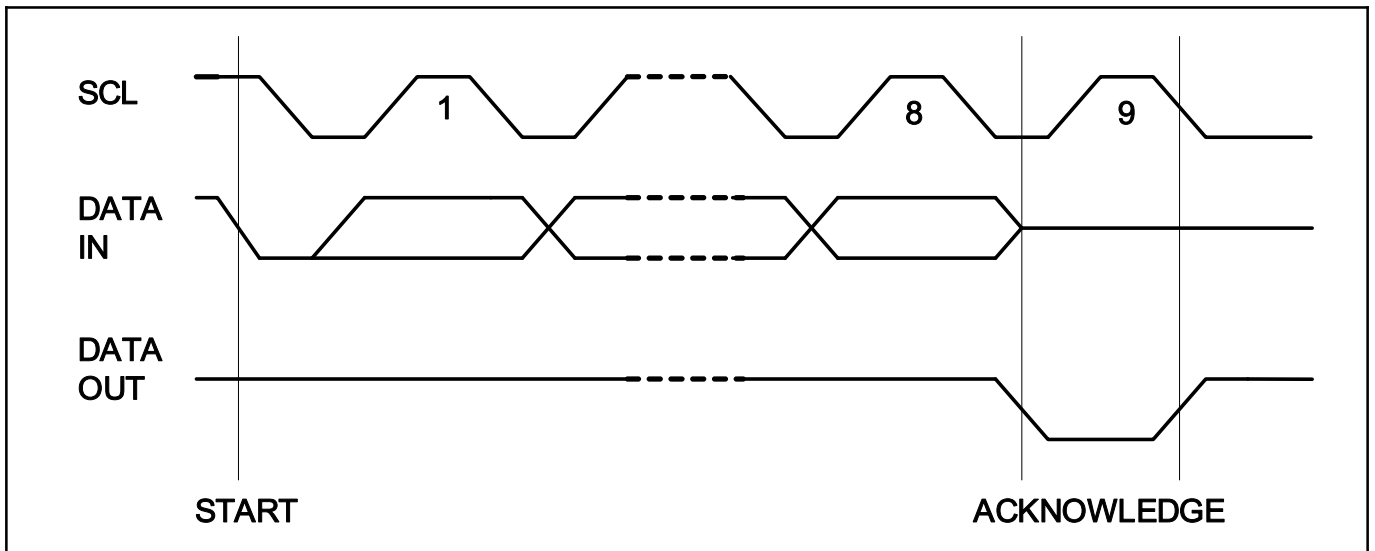
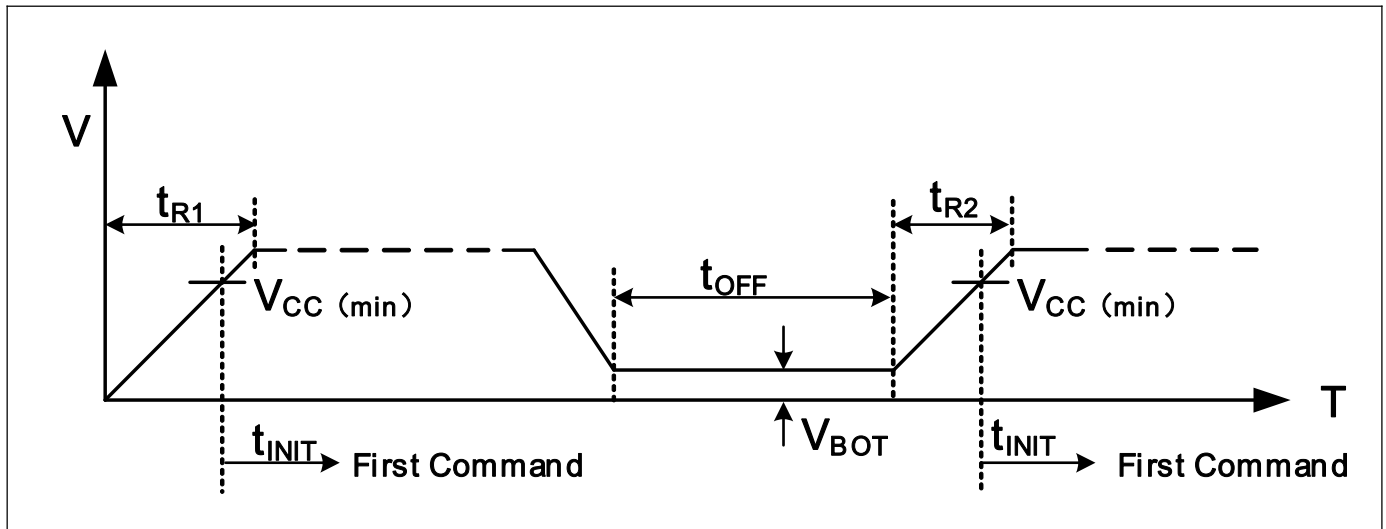


Figure 7. V_{CC} Ramp Up and Ramp Down

Symbol	Parameter	Test Condition	Min	Max	Units
t_{R1}	Power on time from 0V			20	ms
t_{R2}	Power on time from V _{BOT}	V _{BOT} ≤ 0.2V		5	ms
t_{OFF}	power cycle off time		50		ms
t_{INIT}	Time from power on to first command		100		us
V _{BOT}	Power Off threshold for the next power on cycle	No ringback above V _{POFF}		0.2	V

Note: VCC must rise monotonically without ringback.

Device Addressing

The 1024K EEPROM device requires a 8-bit device address word following a start condition to enable the chip for a read or write operation (refer to Figure 8).

The device address word consists of a mandatory one, zero sequence for the first four most significant bits as shown. This is common to all the EEPROM devices.

The 1024K EEPROM uses the two device address bits A2, A1 to allow as many as four devices on the same bus. These bits must compare to their corresponding hard-wired input pins. The A2, A1 pins use an internal proprietary circuit that biases them to a logic low condition if the pins are allowed to float.

The seventh bit (P₀) of the device address is a memory page address bit. This memory page address bit is the most significant bit of the data word address that follows.

The Module package device address word also

consists of a mandatory one, zero sequence for the first four most significant bits. The next 3 bits are all zero.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the device will return to a standby state.

NOISE PROTECTION: Special internal circuitry placed on the SDA and SCL pins prevent small noise spikes from activating the device.

DATA SECURITY: The FM24C1024A has a hardware data protection scheme that allows the user to write protect the entire memory when the WP pin is at V_{CC}.

Write Operations

BYTE WRITE: A write operation requires two 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally-timed write cycle, t_{WR} , to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (refer to Figure 9).

PAGE WRITE: The 1024K EEPROM is capable of 256-byte page writes.

A page write is initiated the same way as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to 255 more data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the page write sequence with a stop condition (refer to Figure 10).

The data word address lower 8 bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than 256 data words are transmitted to the EEPROM, the data word address will “roll over” and previous data will be overwritten.

ACKNOWLEDGE POLLING: Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero allowing the read or write sequence to continue.

Read Operations

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to one. There are three read operations: current address read, random address read and sequential read.

CURRENT ADDRESS READ: The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address “roll over” during read is from the last byte of the last memory page to the first byte of the first page. The address “roll over” during write is from the last byte of the current page to the first byte of the same page.

Once the device address with the read/write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following stop condition (refer to Figure 13).

RANDOM READ: A random read requires a “dummy” byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following stop condition (refer to Figure 14).

SEQUENTIAL READ: Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will “roll over” and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a zero but does generate a following stop condition (refer to Figure 15).

Figure 8. Device Address

	MSB				LSB			
Plastic Package	1	0	1	0	A ₂	A ₁	P ₀	R/W
Module Package	1	0	1	0	0	0	0	R/W

Figure 9. Byte Write

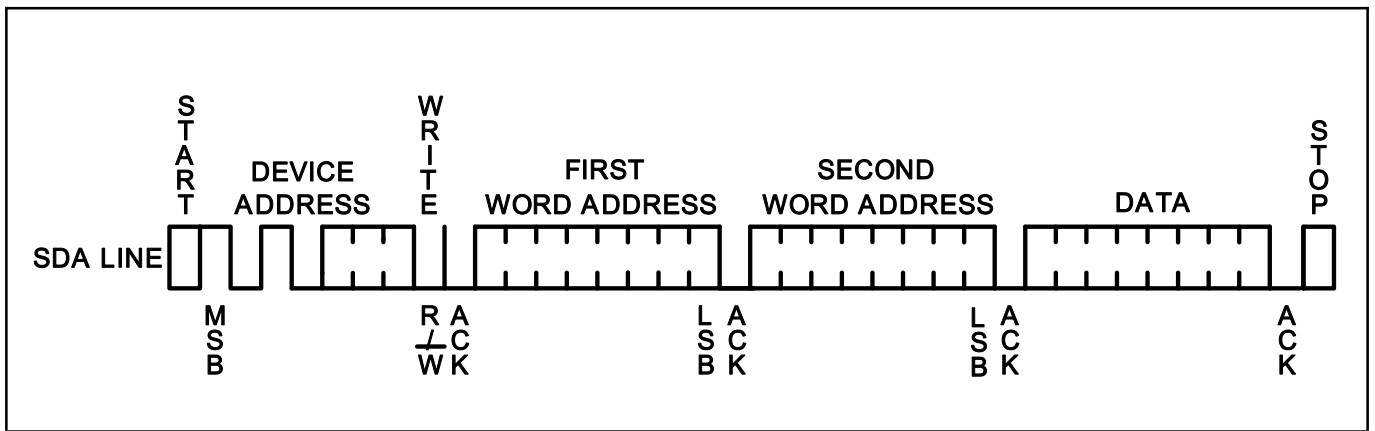


Figure 10. Page Write

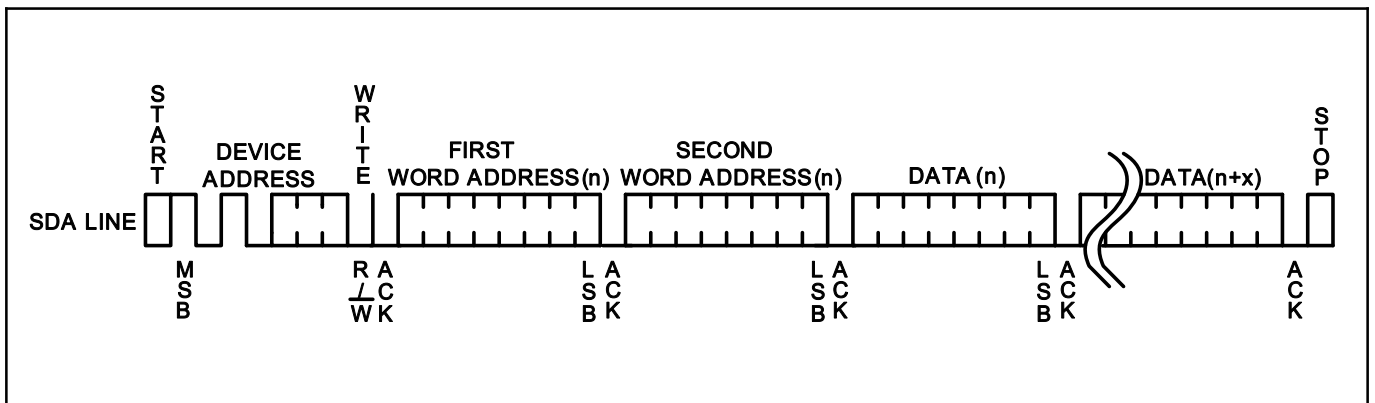


Figure 11. Write-Protect Condition

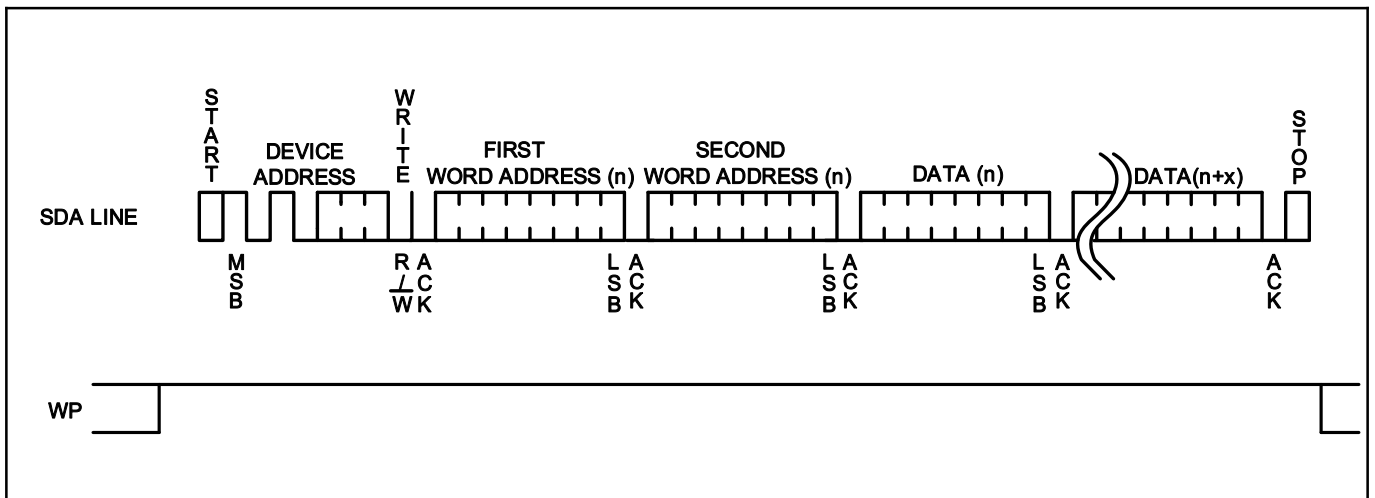


Figure 12. Non-Write-Protect Condition

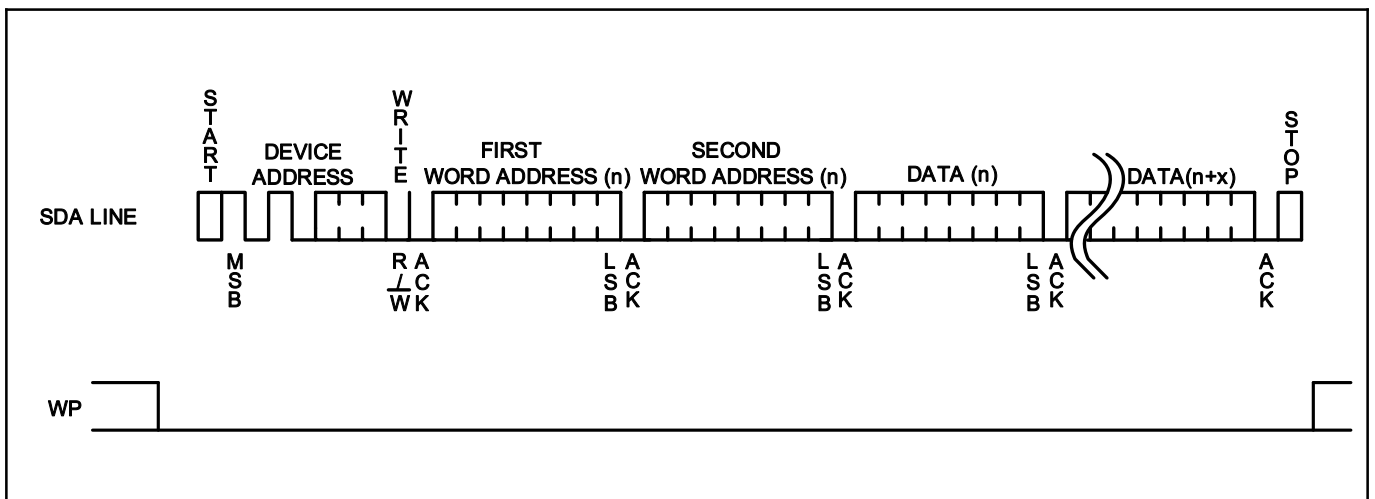


Figure 13. Current Address Read

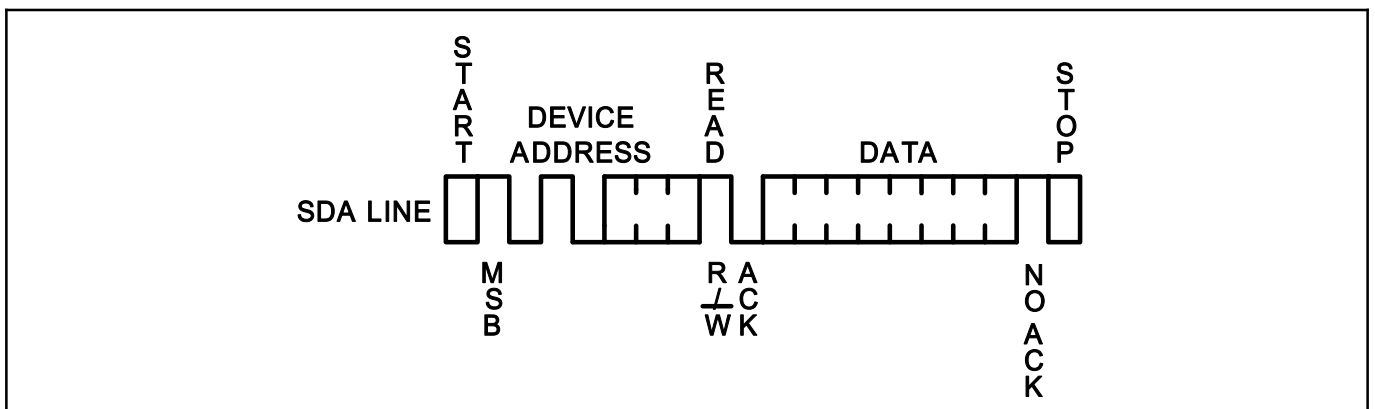


Figure 14. Random Read

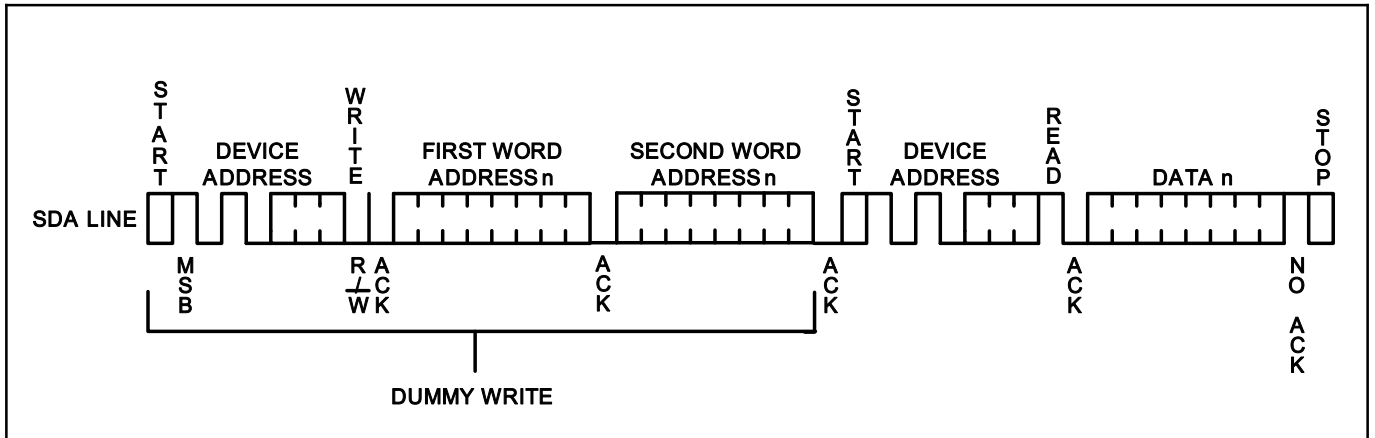
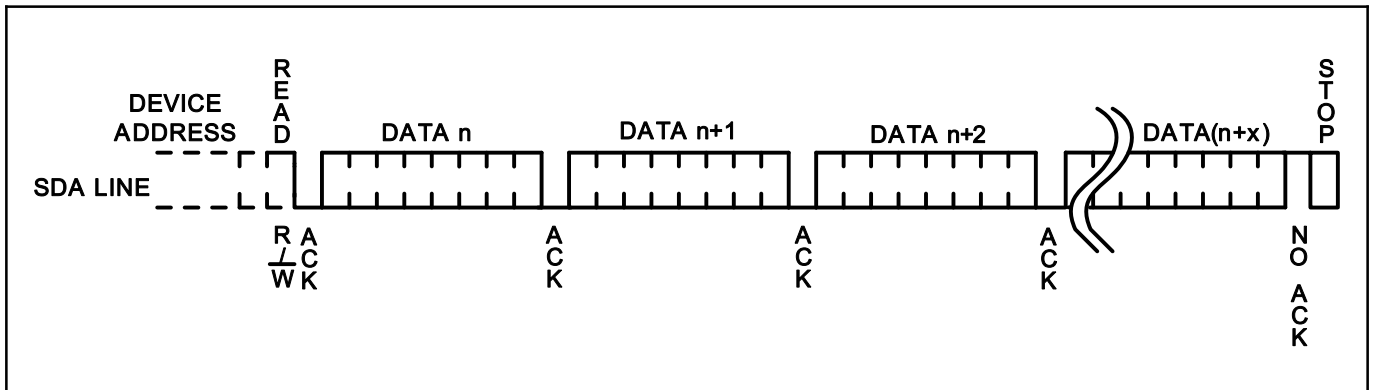


Figure 15. Sequential Read





Ordering Information

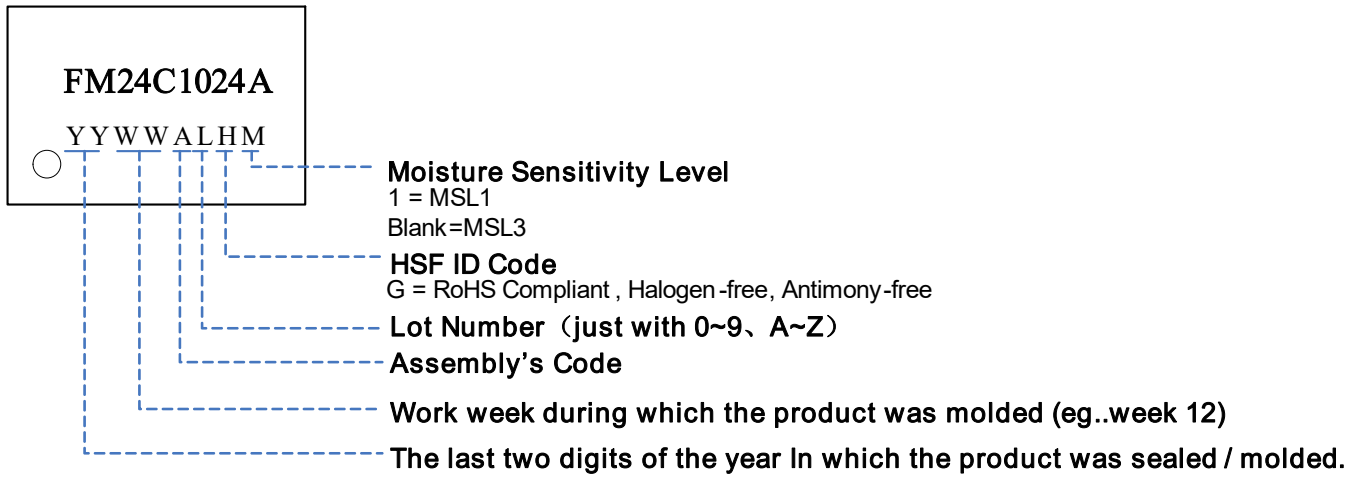
	FM	24C	1024	A	-PP	-C	-H	
Company Prefix								
FM = Fudan Microelectronics Co.,Ltd								
Product Family								
24C = 2-Wire Serial EEPROM								
Product Density								
1024 = 1024K-bit								
Supply Voltage								
A = 1.7V to 5.5V								
Package Type ⁽¹⁾								
SO = 8-pin SOP								M2F or M2P = 8-pin Module Package
TS = 8-pin TSSOP								M3F or M3P = 6-pin Module Package
Product Carrier								
U = Tube								
T = Tape and Reel								
R = Module Reel								
HSF ID Code ⁽²⁾								
Blank or R = RoHS Compliant								
G = RoHS Compliant, Halogen-free, Antimony-free								

Note:

- For the details of Module package and MSL1 package please contact local sales office.
- For M2F, M2P, M3F, M3P package: R class only.

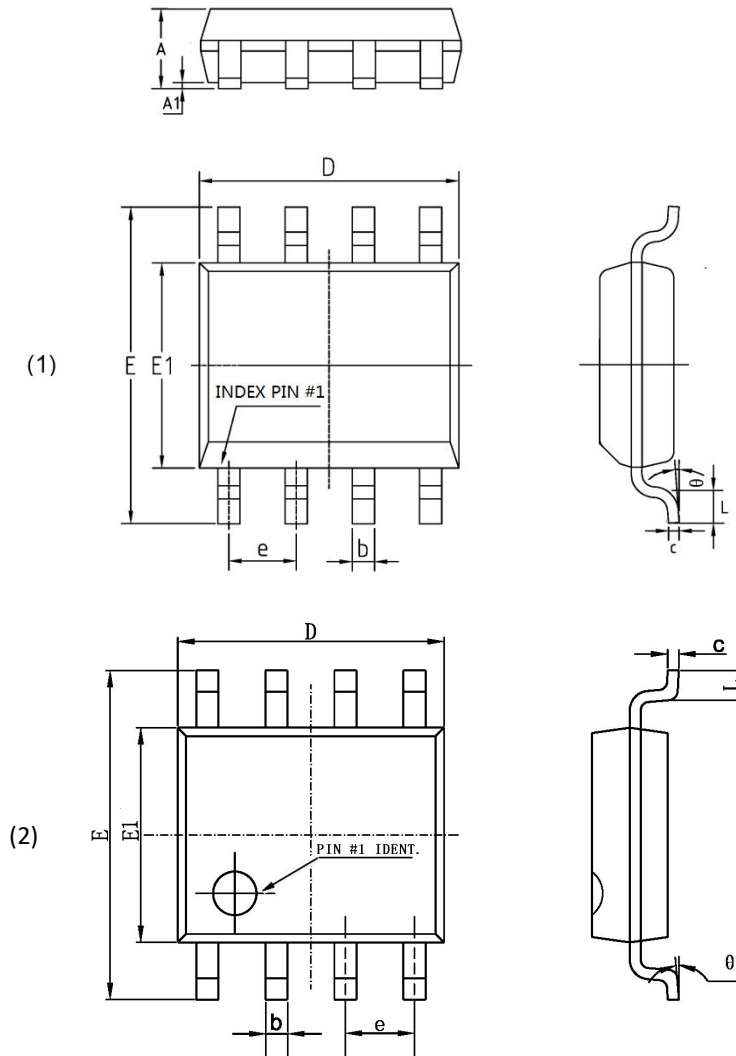
Part Marking Scheme

SOP8



Packaging Information

SOP 8



Symbol	MIN	NOM	MAX
A	1.350	1.550	1.750
A1	0.050	0.150	0.250
b	0.330	0.420	0.510
c	0.150	0.200	0.250
D	4.700	4.925	5.150
E1	3.700	3.900	4.100
E	5.800	6.000	6.200
e	1.270(BSC)		
L	0.400	0.650	0.900
θ	0°	4°	8°

NOTE:

1. Dimensions are in Millimeters.

Revision History

Version	Publication date	Pages	Paragraph or Illustration	Revise Description
	May. 2010	22		Preliminary
0.1	Sep. 2010	20	“DC Characteristics” “Part marking scheme” “Packaging Information”	1. Updated the “DC Characteristics” 2. Added the Module package information 3. Updated the “Part marking scheme” 4. Updated the “Packaging Information”
1.0	May. 2011	20	“AC Characteristics” “Device Addressing” “Sales and Service”	1. Updated the “AC Characteristics”. 2. Updated the “Device Addressing” 3. Updated the address of Beijing office. 4. The company changed its name to Shanghai Fudan Microelectronics Group Co., Ltd.
1.1	Apr. 2013	19	“Disclaimer” “Ordering Information” “Part marking scheme” “Packaging Information”	1. Modified the Disclaimer. 2. Removed PDIP8 Package offering. 3. Updated the “Ordering Information”. 4. Updated the “Part Marking Scheme”. 5. Updated the “Packaging Information”.
1.2	Mar. 2017	19	“Packaging Type” “Ordering Information” “Part marking scheme” “Packaging Information”	1. Change Pin1 name of SOP8 and TSSOP8 from A0 to NC. 2. Updated the “Ordering Information”. 3. Updated the “Part Marking Scheme”. 4. Updated the “Packaging Information”.
1.3	Mar. 2023	22	“Features” “Power-up Timing” “Packaging Information” “AC Characteristics” “Write Protect Description”	1. Add operating temperature description in the “Features” section”. 2. Added Power-up Timing. 3. Updated the “Packaging Information”. 4. Added $t_{WS1}/t_{WH1}/t_{WS2}/t_{WH2}$ AC parameter. 5. Updated Write Protect description.
1.4	Oct.2024	20	“Packaging Type” “Part Marking Scheme” “Packaging Information”	1. Update the “Packaging Type” 2. Update the “Part Marking Scheme” 3. Update the “Packaging Information”



Sales and Service

Shanghai Fudan Microelectronics Group Co., Ltd.

Address: Bldg No. 4, 127 Guotai Rd, Shanghai City
China.

Postcode: 200433

Tel: (86-021) 6565 5050 Fax: (86-021) 6565 9115

Shanghai Fudan Microelectronics (HK) Co., Ltd.

Address: Unit 506, 5/F., East Ocean Centre, 98
Granville Road, Tsimshatsui East, Kowloon, Hong
Kong

Tel: (852) 2116 3288 2116 3338

Fax: (852) 2116 0882

Beijing Office

Address: Room 423, Bldg B, Gehua Building, 1
QingLong Hutong, Dongzhimen Alley north Street,
Dongcheng District, Beijing City, China.

Postcode: 100007

Tel: (86-010) 8418 6608

Fax: (86-010) 8418 6211

Shenzhen Office

Address: Room.2306-2308, Building A7, Chuangzhi
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Postcode: 518000

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Shanghai Fudan Microelectronics (HK) Ltd Taiwan Representative Office

Address: Unit 1225, 12F., No 252, Sec.1 Neihu Rd.,
Neihu Dist., Taipei City 114, Taiwan

Tel : (886-2) 7721 1889

Fax: (886-2) 7722 3888

Shanghai Fudan Microelectronics (HK) Ltd Singapore Representative Office

Address : 47 Kallang Pudding Road, #08-06,The
Crescent @ Kallang ,Singapore 349318

Tel : (65) 6443 0860

Fax: (65) 6443 1215

Fudan Microelectronics (USA) Inc.

Address : 97 E Brokaw Road, Suite 320, San Jose, CA
95112

Tel : (+1)408-335-6936

Web Site: <http://www.fmsh.com/>